

### **INCHANGE SEMICONDUCTOR**

### isc N-Channel MOSFET Transistor

## IXTP120N075T2

#### D FEATURES · Static drain-source on-resistance: $R_{DS}(on) \le 7.7 m_{\Omega} @V_{GS} = 10V$ · Fully characterized avalanche voltage and current 100% avalanche tested Minimum Lot-to-Lot variations for robust device pin 1, Gate performance and reliable operation 2, Drain 123 3, Source TO-220C package APPLICATION DC/DC Converters S · High Current Switching Applications ABSOLUTE MAXIMUM RATINGS(Ta=25°C) SYMBOL PARAMETER VALUE UNIT VDSS **Drain-Source Voltage** 75 V V V<sub>GS</sub> Gate-Source Voltage $\pm 20$ Drain Current-Continuous 120 $I_D$ А с Drain Current-Single Pulsed 300 А **I**DM mm DIM MIN MAX $P_{D}$ Total Dissipation @Tc=25°C 250 W 15.90 15.50 А 9.90 10.20 В **Operating Junction Temperature** -55~175 °C С 4.20 4.50 Τį D 0.70 0.90F 3.40 3.70 Storage Temperature -55~175 °C G Tstg 4.98 5.18Н 2.68 2.90J 0.44 0.60 13.00 K 13.40 THERMAL CHARACTERISTICS 1.10 1.45 L 2.70 Q 2.90

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SYMBOL	PARAMETER	MAX	UNIT		
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	0.6	°C/W		

2.30

1.29

6.45

8.66

R

S

U

v

2.70

1.35

6.65

8.86

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#### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID = 250 μ A	75		V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID = 250 μ A	2.0	4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 60A		7.7	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V		±200	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		5	- μ <b>Α</b>
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;TJ= 150℃		150	
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> = 98A; V <sub>GS</sub> = 0V		1.5	V

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